

| Ref # | Hits | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|---|---|------------------|---------|------------------|
| L4    | 2    | "20040181761"   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/12/08 10:33 |
| L5    | 9    | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) same ((measur\$3 or obtain\$3) near3 (parameter or charactersitic or electric\$3)) same transistor same gate and (simulat\$3 or SPICE)                           | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/12/08 11:33 |
| L6    | 7    | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) same ((measur\$3 or obtain\$3) near3 (parameter or charactersitic or electric\$3)) same transistor same gate same (simulat\$3 or SPICE)                          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/12/08 11:48 |
| L7    | 4    | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE)                           | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/12/08 11:57 |
| L8    | 231  | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE)                            | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/12/08 12:04 |
| L9    | 16   | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate same (simulat\$3 or SPICE)                           | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/12/08 11:58 |
| L10   | 65   | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/12/08 12:06 |

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| L11 | 57 | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor)                                  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 12:08 |
| L12 | 58 | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor)          | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 12:09 |
| L13 | 23 | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor)                        | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 12:14 |
| L14 | 1  | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic or parameter or electric\$3)) and (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same (matrix or array) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 12:16 |
| L15 | 0  | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic or parameter or electric\$3)) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor) and (matrix or array) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 12:17 |

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|-----|--------|---|---|----|----|------------------|
| L16 | 0      | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (first adj transistor) and (second adj transistor) and (matrix or array)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 12:18 |
| L17 | 1      | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3) same (transistor near3 (arrang\$3 or plac\$3 or rearrang\$3 or dispos\$3 or array or position\$3 or locat\$3 or resid\$3)) same gate and (simulat\$3 or SPICE) and (matrix or array))  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:06 |
| L19 | 2      | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3) same (transistor near3 (matrix or array)) same gate and (simulat\$3 or SPICE))   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:30 |
| L20 | 5      | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) same (characteristic or parameter or electric\$3) same (transistor near3 (matrix or array)) and (simulat\$3 or SPICE) and (gate same (matrix or (two adj dimensional adj pattern)))  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 13:32 |
| S1  | 1      | simulat\$3 same transistor same (matrix adj pattern)  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 08:48 |
| S2  | 2      | simulat\$3 same transistor same (matrix near3 pattern)  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 08:49 |
| S3  | 991648 | simulat\$3 same transistor same matrix same (characteristic parameter) and gate   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 15:38 |
| S4  | 31     | simulat\$3 same transistor same matrix same (characteristic parameter) and gate   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 09:58 |

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|-----|----|--|---|----|----|------------------|
| S5  | 1  | simulat\$3 same transistor same matrix same (characteristic parameter) same position and (gate same (length width))  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 09:19 |
| S6  | 4  | simulat\$3 same transistor same matrix same (characteristic parameter) same (position area region plac\$3) and (gate same (length width))  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 09:21 |
| S7  | 5  | simulat\$3 same transistor same matrix same (characteristic parameter) same (position area region plac\$3 arrang\$3 arrangement) and (gate same (length width))  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 09:22 |
| S8  | 12 | simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4)  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 10:05 |
| S9  | 2  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4) and ((first adj transistor) same (measur\$3 comput\$3 calculat\$3))                                    | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 10:07 |
| S10 | 2  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4) and ((first adj transistor) same (measur\$3 comput\$3 calculat\$3)) and (predict\$3 determin\$3)       | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 10:08 |
| S11 | 4  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (threshold near3 volt\$4) and (first adj transistor)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 10:19 |
| S12 | 3  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate same (threshold near3 volt\$4) and ((first and second and third) adj transistor)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 12:14 |
| S13 | 2  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate same (threshold near3 volt\$4) and ((first near3 transistor) same (measur\$3 determin\$3)) and ((second and third) near3 transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 12:40 |

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| S14 | 1  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate same (threshold near3 volt\$4) and ((first near3 transistor near3 model) same (measur\$3 determin\$3)) and ((second and third) near3 transistor near3 model) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 12:44 |
| S15 | 1  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate same volt\$4 and ((first near3 transistor near3 model) same (measur\$3 determin\$3)) and ((second and third) near3 transistor near3 model)                   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 12:48 |
| S16 | 2  | simulat\$3 same transistor same matrix same (characteristic parameter) and ((first near3 transistor) near3 (measur\$3 determin\$3))  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 14:34 |
| S17 | 3  | simulat\$3 same transistor same (matrix array) same (characteristic parameter) and ((first near3 transistor) near3 (measur\$3 determin\$3))  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 14:36 |
| S18 | 10 | simulat\$3 same transistor same (matrix array) same (characteristic parameter) and ((first near3 transistor) same (measur\$3 determin\$3))   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 14:51 |
| S19 | 14 | simulat\$3 same transistor same (arrang\$3 plac\$3 plan\$4) same (matrix array) same (characteristic parameter)  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 14:53 |
| S20 | 8  | simulat\$3 same transistor same (arrang\$3 plac\$3 plan\$4) same (matrix array) same (characteristic parameter) same gate  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 14:54 |
| S21 | 4  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate and interpolat\$3  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 07:56 |
| S22 | 0  | simulat\$3 same transistor same matrix same (characteristic parameter) same predict\$3 same measur\$3 and gate and interpolat\$3   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 15:48 |

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| S23 | 0   | simulat\$3 same transistor same matrix same (characteristic parameter) same predict\$3 same measur\$3 and gate                                      | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 15:55 |
| S24 | 1   | simulat\$3 same transistor same matrix same (characteristic parameter) same ((predict\$3 or interpolat\$3) near3 measur\$3) and gate                | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 15:55 |
| S25 | 1   | simulat\$3 same transistor same matrix same (characteristic parameter) and ((predict\$3 or interpolat\$3) near3 measur\$3) and gate                 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/05 15:55 |
| S26 | 13  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate and (interpolat\$3 or predict\$3)                                   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 08:03 |
| S27 | 12  | simulat\$3 same transistor same matrix same (characteristic parameter) and gate and ((interpolat\$3 or predict\$3) same (characteristic parameter)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 09:57 |
| S28 | 2   | simulat\$3 same transistor same matrix and gate and ((interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3)                  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:17 |
| S29 | 101 | (interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:18 |
| S30 | 43  | (interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:25 |
| S31 | 19  | (interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate same volt\$3                                 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:18 |
| S32 | 0   | (interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate same matrix                                  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:19 |

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| S33 | 6  | (interpolat\$3 or predict\$3) same (characteristic parameter) same measur\$3 same transistor same gate same (matrix or array or pattern)  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:24 |
| S34 | 0  | (interpolat\$3 or predict\$3) near3 (characteristic parameter) same measur\$3 same transistor same gate same (matrix or array or pattern)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:24 |
| S35 | 8  | (interpolat\$3 or predict\$3) near3 (characteristic parameter) same measur\$3 same transistor same gate   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 10:44 |
| S36 | 1  | "6723665".PN.   | USPAT; USOCR                                | OR | ON | 2005/12/07 10:36 |
| S37 | 1  | "5323343".PN.   | USPAT; USOCR                                | OR | ON | 2005/12/07 10:40 |
| S38 | 15 | (interpolat\$3 or predict\$3) near3 (characteristic parameter) same measur\$3 same transistor and gate  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 11:05 |
| S39 | 11 | ((interpolat\$3 or predict\$3) near3 (characteristic parameter)) same ((measur\$3 or simulat\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor and gate                              | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 11:06 |
| S40 | 4  | ((interpolat\$3 or predict\$3) near3 (characteristic parameter)) same ((measur\$3 or simulat\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor same gate                             | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 13:44 |
| S41 | 11 | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3) near3 (characteristic parameter)) same ((measur\$3 or simulat\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor same gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/07 14:53 |
| S42 | 12 | ((interpolat\$3 or predict\$3 or estimat\$3 or evaluat\$3 or simulat\$3) near3 (characteristic parameter)) same ((measur\$3 or obtain\$3) near3 (parameter charactersitic)) same transistor same gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/12/08 11:30 |